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NTE6093 Silicon Rectifier Dual, Schottky Barrier

Description:

The NTE6093 is a silicon rectifier in a TO3P type package designed using the Schottky Barrier principle with a Molybdenum barrier metal.

Features:

- Low Forward Voltage
- Guard-Ring for Stress Protection
- Low Power Loss & High Efficiency
- Guarantee Reverse Avalanche
- +125°C Operating Junction Temperature
- High Surge Capacity
- Low Stored Charge majority Carrier Conduction
- Low Switching Noise

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}	60V
Working Peak Reverse Voltage, V_{RWM}	60V
DC Blocking Voltage, V_R	60V
RMS Reverse Voltage, $V_{R(RMS)}$	42V
Average Rectifier Forward Current ($V_R = 60V$, $T_C = +125^\circ C$), $I_{F(AV)}$	
Per Diode	30A
Total Device	60A
Peak Repetitive Forward Current ($V_R = 60V$, Square Wave, $T_C = +125^\circ C$), I_{FM}	60A
Non-Repetitive Peak Surge Current, I_{FSM}	
(Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60Hz)	600A
Operating Junction Temperature Range, T_J	-65° to +125°C
Storage Temperature Range, T_{stg}	-65° to +125°C



Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	V_F	$I_F = 30A$, $T_C = +25^{\circ}C$	—	—	0.63	V
		$I_F = 30A$, $T_C = +125^{\circ}C$	—	—	0.75	V
Instantaneous Reverse Current	I_R	$V_R = 60V$, $T_C = +25^{\circ}C$	—	—	10	μA
		$V_R = 60V$, $T_C = +100^{\circ}C$	—	—	150	μA

